
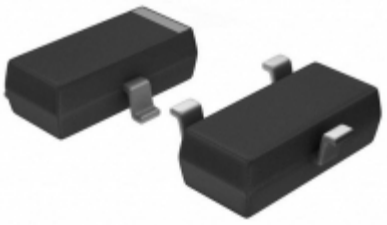







	<h2>SI2334DS-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI2334DS-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 4.9A SOT-23</p> <p>Datenblätter:  SI2334DS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 55898 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2334DS-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 30V 4.9A SOT-23
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	55898 pcs Stock
detaillierte Beschreibung	N-Channel 30V 4.9A (Tc) 1.3W (Ta), 1.7W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	1.3W (Ta), 1.7W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.9A (Tc)
Rds On (Max) @ Id, Vgs	44 mOhm @ 4.2A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	10nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	634pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	2.5V, 4.5V
Vgs (Max)	±8V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI2334DS-T1-GE3CT


SI2334DS-T1-GE3 ist neu im Original, Suche SI2334DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2334DS-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2334DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2333DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 4.1A SOT23-3</p>	 <p>SI2334DS-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 4.9A SOT-23</p>	 <p>SI2333DS-T1-E3 Vishay / Siliconix MOSFET P-CH 12V 4.1A SOT23-3</p>	 <p>SI2333DS-T1-GE3 Vishay / Siliconix MOSFET P-CH 12V 4.1A SOT23-3</p>
 <p>SI2335DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 3.2A SOT23-3</p>	 <p>SI2333DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 4.1A SOT23-3</p>	 <p>SI2335DS-T1-E3 Vishay / Siliconix MOSFET P-CH 12V 3.2A SOT23</p>	 <p>SI2334DS-T1-E3 V SI2334DS-T1-E3 V</p>

heiße Teile

Mehr

 SI2328DS-T1-GE3	 SI2329DS-T1-E3	 SI2329DS-T1-GE3	 SI2329DS-T1-GE3	 SI2331DS
 SI2331DS-T1-E3	 SI2331DS-T1-E3	 SI2331DS-T1-GE3	 SI2331DS-T1-GE3	 SI2333ADS-T1-GE3
 SI2333CDS	 SI2333CDS-T1-E3	 SI2333CDS-T1-E3	 SI2333CDS-T1-GE3	 SI2333CDS-T1-GE3
 SI2333DDS-T1-E3	 SI2333DDS-T1-GE3	 SI2333DDS-T1-GE3	 SI2333DS	 SI2333DS-T1-E3
 SI2333DS-T1-E3	 SI2333DS-T1-GE3	 SI2333DS-T1-GE3	 SI2334DS-T1-E3	 SI2334DS-T1-GE3
 SI2335DS-T1	 SI2335DS-T1-E3	 SI2335DS-T1-E3	 SI2335DS-T1-GE3	 SI2335DS-T1-GE3
 SI2336DS-T1-E3	 SI2336DS-T1-GE3	 SI2336DS-T1-GE3	 SI2337DS	 SI2337DS-T1-E3
 SI2337DS-T1-E3	 SI2337DS-T1-GE3	 SI2337DS-T1-GE3	 SI2338DS-T1-E3	 SI2338DS-T1-GE3
 SI2338DS-T1-GE3	 SI2341DS	 SI2341DS-T1-E3	 SI2341DS-T1-E3	 SI2341DS-T1-GE3
 SI2341DS-T1-GE3	 SI2342DS-T1-E3	 SI2342DS-T1-GE3	 SI2342DS-T1-GE3	 SI2343ADS-T1-GE3

Contact us:Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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